2SK2127

Silicon N-Channel Power F-MOS

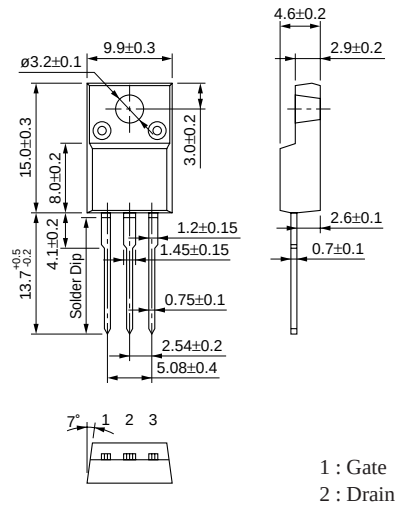
■ Features

- Avalanche energy capability guaranteed : EAS > 130mJ
- V_{GSS}=±30V guaranteed
- High-speed switching : t_f= 60ns
- No secondary breakdown

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

Unit : mm



1 : Gate
2 : Drain
3 : Source
TO-220E Package

■ Absolute Maximum Ratings (Tc = 25˚C)

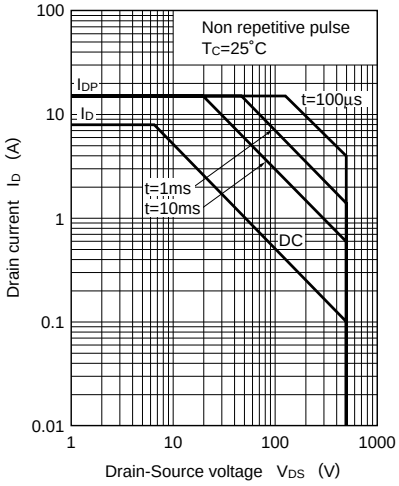
Parameter		Symbol	Rating	Unit
Drain-Source breakdown voltage		V_{DSS}	500	V
Gate-Source voltage		V_{GSS}	±30	V
Drain current	DC	I_D	±8	A
	Pulse	I_{DP}	±16	A
Avalanche energy capability		EAS *	130	mJ
Allowable power dissipation	T_C= 25˚C	P_D	50	W
	Ta= 25˚C		2	
Channel temperature		T_{ch}	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

* L= 5mH, I_L= 7.3A, V_{DD}= 50V, 1 pulse

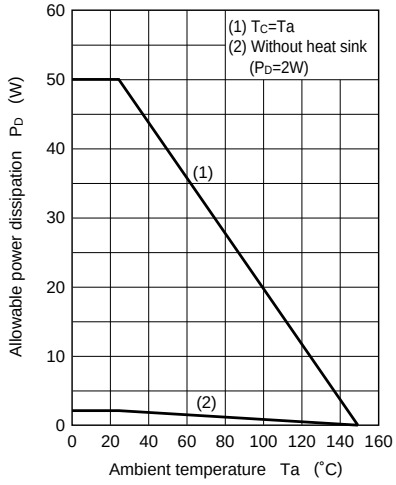
■ Electrical Characteristics (Tc = 25˚C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	V_{DS}= 400V, V_{GS}= 0			0.1	mA
Gate-Source leakage current	I_{GSS}	V_{GS}=±30V, V_{DS}= 0			±1	μ A
Drain-Source breakdown voltage	V_{DSS}	I_D=1mA, V_{GS}= 0	500			V
Gate threshold voltage	V_{th}	V_{DS}= 25V, I_D=1mA		2	5	V
Drain-Source ON-resistance	$R_{DS(on)}$	V_{GS}=10V, I_D= 4A		0.7	1	Ω
Forward transadmittance	$\|Y_{fs}\|$	V_{DS}= 25V, I_D= 4A	3	5		S
Diode forward voltage	V_{DSF}	I_{DR}= 8A, V_{GS}= 0			–1.6	V
Input capacitance	C_{iss}	V_{DS}= 20V, V_{GS}= 0, f=1MHz		1200		pF
Output capacitance	C_{oss}			160		pF
Feedback capacitance	C_{rss}			70		pF
Turn-on time (delay time)	$t_{d(on)}$	V_{GS}=10V, I_D= 4A V_{DD}=150V, R_L= 37.5Ω		30		ns
Rise time	t_r			70		ns
Fall time	t_f			60		ns
Turn-off time (delay time)	$t_{d(off)}$			140		ns
Channel-Case heat resistance	$R_{th(ch-c)}$				2.5	˚C/W

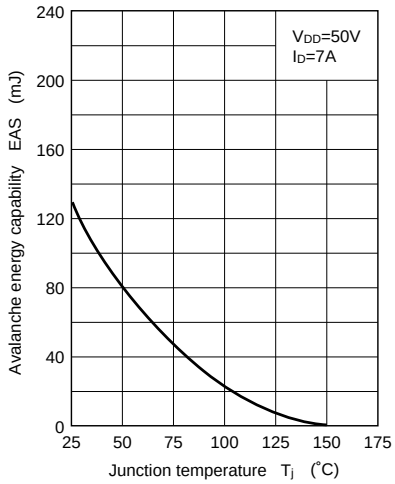
Area of safe operation (ASO)



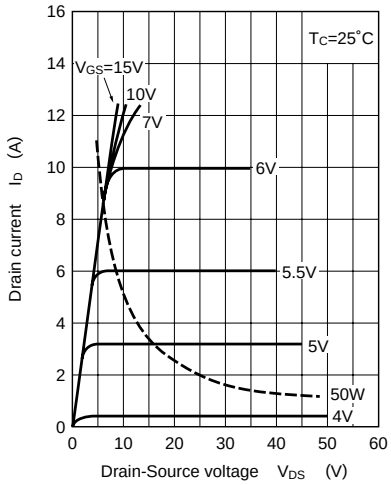
P_D – Ta



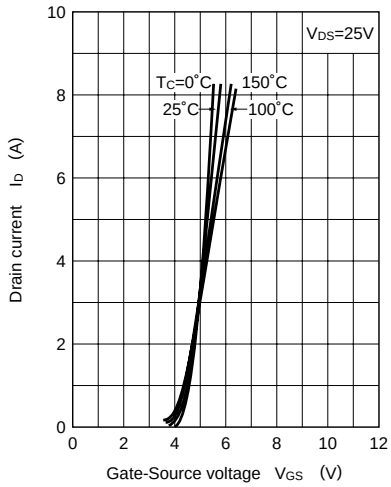
EAS – T_j



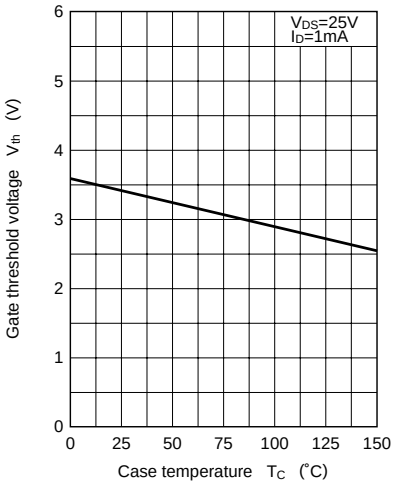
I_D – V_{DS}



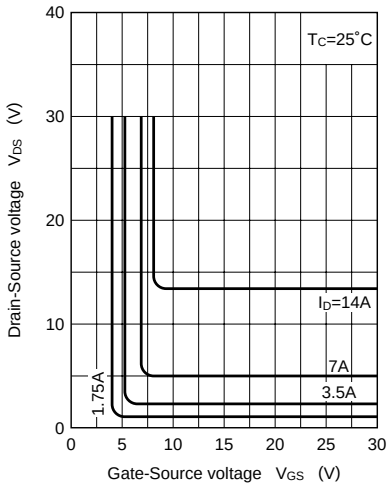
I_D – V_{GS}



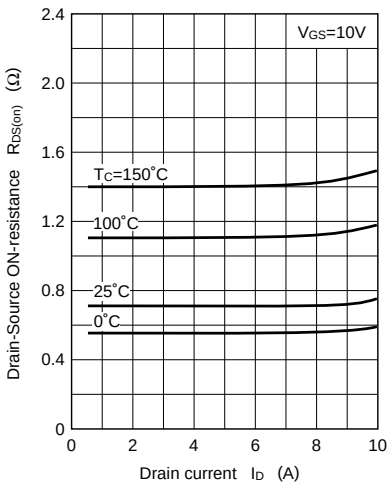
V_{th} – T_C



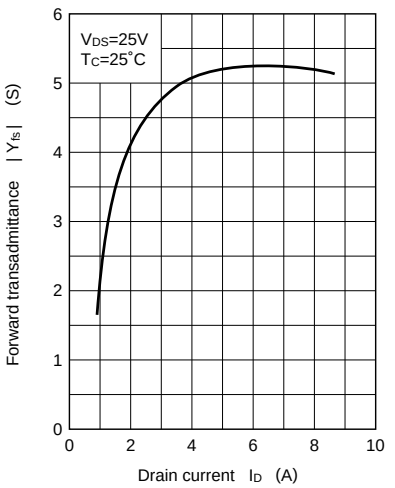
V_{DS} – V_{GS}



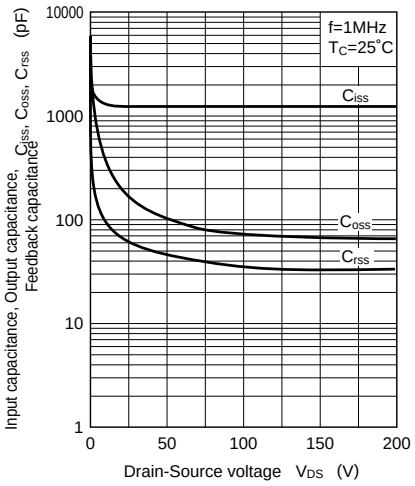
$R_{DS(on)}$ – I_D



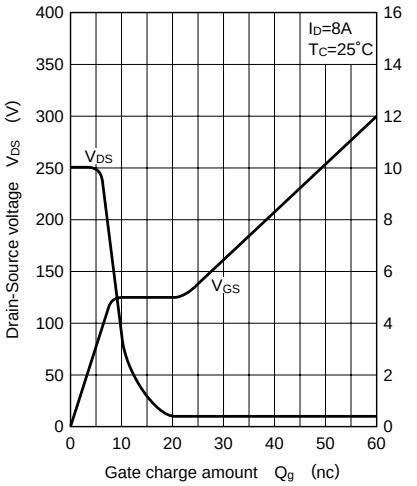
| Y_{fs} | – I_D



$C_{iss}, C_{oss}, C_{rss} - V_{DS}$



$V_{DS}, V_{GS} - Q_g$



$t_{d(on)}, t_r, t_f, t_{d(off)} - I_D$